Exchange-Coupling-Induced Symmetry Breaking in Topological Insulators

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<td>As Published</td>
<td><a href="http://dx.doi.org/10.1103/PhysRevLett.110.186807">http://dx.doi.org/10.1103/PhysRevLett.110.186807</a></td>
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<tr>
<td>Publisher</td>
<td>American Physical Society</td>
</tr>
<tr>
<td>Version</td>
<td>Final published version</td>
</tr>
<tr>
<td>Accessed</td>
<td>Fri Feb 08 08:13:02 EST 2019</td>
</tr>
<tr>
<td>Citable Link</td>
<td><a href="http://hdl.handle.net/1721.1/81329">http://hdl.handle.net/1721.1/81329</a></td>
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An exchange gap in the Dirac surface states of a topological insulator (TI) is necessary for observing the predicted unique features such as the topological magnetoelectric effect as well as to confine Majorana fermions. We experimentally demonstrate proximity-induced ferromagnetism in a TI, combining a ferromagnetic insulator EuS layer with \( \text{Bi}_2\text{Se}_3 \), without introducing defects. By magnetic and magneto-transport studies, including anomalous Hall effect and magnetoresistance measurements, we show the emergence of a ferromagnetic phase in TI, a step forward in unveiling their exotic properties.

Three-dimensional topological insulators (TIs) are materials carrying surface states protected by time-reversal symmetry [1,2]. The short-range nature of magnetic proximity coupling with a ferromagnetic insulator (FI) allows the TI surface states to experience the ferromagnetic interactions, where the symmetry breaking happens right at the interface [3–6], rather than affecting the majority bulk states or introducing defects. The well-behaved Heisenberg FI, such as EuS, is an excellent candidate to isolate the magnetic response of the surface states from the parallel conduction of the TI bulk material. Furthermore, the local time-reversal symmetry breaking is essential for inducing a quantized topological magnetoelectric response [7]. This may be used to investigate interesting emergent phenomena, such as the zero-field half-integer quantum Hall effect [7], the topological magnetoelectric effect [7,8], and the magnetic monopole [9] to name a few.

Experimentally the most common method of introducing ferromagnetic order in TI is by doping with specific elements; in this case, it is hard to separate the surface and the bulk phases [10–14]. Although a surface ferromagnetic order is shown achievable by uniformly depositing magnetic atoms, i.e. Fe, over the TI surface [15,16], the transport properties of a TI can be influenced by the metallic ferromagnetic overlayer or atoms. Besides, the doping of magnetic elements inevitably introduces crystal defects, magnetic scattering centers, as well as impurity states in the insulating gap, which are detrimental to mobility and the transport of spin-momentum locked surface electrons in TIs [1]. From the point of view of confining Majorana fermions in topological superconductors [17,18], the exchange field of a FI is capable of lifting the spin degeneracy without destroying the superconductivity pairing [5,6]. This is in contrast to the adverse effects resulting from the introduction of magnetic impurities. In combination with a FI, the Majorana bound states can be well established on the top surface of a superconducting TI [19] or superconducting proximity-coupled TI [20].

Here, we introduce ferromagnetic order onto the surface of \( \text{Bi}_2\text{Se}_3 \) thin films by using the FI EuS [Fig. 1(a)] forming \( \text{Bi}_2\text{Se}_3/\text{EuS} \) heterostructures. Ultrathin FI EuS layers are stable with good growth characteristics and a clean interface on a variety of materials; they form excellent tunnel barriers even down to 1 nm thickness showing near ideal...
area coverage [5,6,21,22]. Although the magnetic proximity effect of EuS on a superconductor has been clearly demonstrated [5], its effectiveness on the TI Dirac surface state is an open question. This exchange phenomenon can be expected to have a profound influence on the novel surface Dirac electron system, especially the spin-momentum locked helical electronic states in TIs [1,23,24]. Achieving this is nontrivial as it critically depends on the control of the TI/EuS heterostructures interface down to the last atomic layer to be able to transmit the exchange interaction across the interface. This also depends on the growth condition of EuS on bismuth compounds.

The bilayer structure growth was carried out in a molecular beam epitaxy apparatus in an ultrahigh vacuum environment (low 10^{-10} torr). Thin film Bi$_2$Se$_3$ were epitaxially grown on Si(111) or Al$_2$O$_3$(0001) substrates by coevaporating high-purity Bi and Se constituents from separate conventional Knudsen cells at 450 K. EuS was grown in situ on Bi$_2$Se$_3$ from a single e-beam source at room temperature, followed by a capping layer of 4 nm amorphous Al$_2$O$_3$. The quality of the layers were confirmed by high-resolution x-ray diffraction, using 1.54 Å Cu-K$_{α1}$ radiation, which was also used to confirm the thickness and smoothness of the grown layers. Figure 1(b) shows the x-ray diffraction characterizations revealing the single phase of hexagonal Bi$_2$Se$_3$ and cubic EuS indicating the epitaxial growth without any clustering. The growth relations on sapphire and silicon substrates are Al$_2$O$_3$(0001)// Bi$_2$Se$_3$(0001)//EuS[111] and Si[111]/Bi$_2$Se$_3$(0001)//EuS[111]. Low angle x-ray reflectivity studies confirmed a sharp Bi$_2$Se$_3$/EuS interface.

Several samples were grown simultaneously with a shadow mask technique. The Bi$_2$Se$_3$ layer thickness was fixed at 20 nm, while the EuS film thickness was varied locally (1, 3, 5, 7, and 10 nm in different lateral sections of the same Bi$_2$Se$_3$ film). Further, a sample of 1 nm EuS on Si(111) was also grown in situ forming a set of TI/FI bilayer samples and a single layer control sample for the studies. For transport measurements, control samples of Bi$_2$Se$_3$ thin films capped with Al$_2$O$_3$ were grown simultaneously. While the control samples did not display magnetic behavior, they showed typical weak antilocalization (WAL) effect under a perpendicular magnetic field (only a weak field dependence, and no WAL, for in-plane magnetic field) and with no hysteresis, as seen by others [25,26] as well as our previous observations [27]. The samples were patterned into standard Hall bar devices with a channel width of 60 μm and channel length of 400 μm. The charge carriers of the Bi$_2$Se$_3$ layers were determined to be n type with a density ($n_{3D}$) $\sim$ 4 $\times$ 10^{19} cm$^{-3}$ at 4.2 K, which was not sensitive to the EuS capping. For several samples (both control and bilayer samples), temperature dependence of $n_{3D}$ was monitored. We found only a small decrease (1% in $n_{3D}$ as the temperature went below 40 K, with the most decrease occurring below 10 K in both bilayer and control samples. No significant change was observed for $n_{3D}$ across $T_C$ in bilayer samples due to the development of interface ferromagnetism. The large background contribution from the bulk conductivity could have precluded observing any changes across $T_C$.

The magnetic properties of the Bi$_2$Se$_3$/EuS heterostructures were determined by magnetization measurements, performed in a Quantum Design Magnetic Property Measurement System. All TI/FI bilayer samples exhibit ferromagnetic phase transitions when the temperature decreases below about 20 K [Fig. 2(a) inset]. Also shown here is the magnetic hysteresis loop with a sizeable remnant magnetization and coercive field $H_C$ indicating an in-plane easy axis. The $T_C$ was estimated from the point at which the slope of M vs T data sharply increased. It may be noted that the $T_C$ is influenced by the applied field during cooling (unless this field is very small) as well as due to high carrier density. These factors can raise $T_C$ above the bulk $T_C$ of EuS [28].

In the following we demonstrate that EuS induces a significant magnetic moment on the surface of the Bi$_2$Se$_3$ film. Figure 2(a) shows the measured magnetic moment of

![FIG. 2 (color online). (a) Magnetic moment per Eu$^{2+}$ ion as a function of magnetic field of Bi$_2$Se$_3$/EuS bilayer samples for three thicknesses of EuS: 1 nm (black squares), 3 nm (red circles), and 7 nm (blue up triangles), measured at 4.8 K. The magnetic field was applied in the film plane. The control sample data for 1 nm EuS on Si(111) are shown in green down triangles. The inset shows the temperature dependence of the magnetic moment, and the low-field hysteresis for the Bi$_2$Se$_3$/EuS (3 nm) sample. (b) Saturation magnetic moment per unit area (see text) as a function of the thickness of the EuS layers, where the nonzero intercept is the induced interfacial magnetic moment. The size of the data points includes the error in M and film thickness. The inset shows the saturation magnetic moment at 1.5 kOe per Eu$^{2+}$ ion as a function of EuS thickness.](186807-2)
three bilayer samples having varying thicknesses and a control sample of Si(111)/EuS. It is striking that for all Bi$_2$Se$_3$/EuS samples, each Eu$^{2+}$ ion contributes a saturation magnetic moment $M_L$ that is higher than the $7\mu_B$ upper limit of EuS [6]. Moreover, $M_L$ increases as the thickness of the EuS layer decreases (inset of Fig. 2b). It reaches a maximum of $11.3\mu_B$/Eu$^{2+}$ in the bilayer sample with 1 nm EuS, which is 60% larger than the $7\mu_B$/Eu$^{2+}$ value [6]. It may be noted that the maximum number of deposited EuS molecules was monitored by the quartz sensor. Since the excess moment cannot be accounted for by the EuS layer alone, its origin is attributed to the induced moment at the Bi$_2$Se$_3$/EuS interface. On the other hand, the control sample shows an $M_L$ of 5.9$\mu_B$/Eu$^{2+}$ [Fig. 2(a)], indicating that the enhanced moment seen in the Bi$_2$Se$_3$/EuS bilayer is not due to the EuS layer or the film thickness-related properties. Furthermore, EuS shows more favorable clustering of EuS or Eu atoms is ruled out (cross-sectional SEM studies prove this) as it cannot provide an increase of the magnetic moment. It may be noted that we can form excellent tunnel barriers even down to 0.8 nm of EuS showing standard tunneling characteristics including Josephson tunneling in other systems [6].

The above magnetization studies indicate that the interface region of Bi$_2$Se$_3$ becomes magnetized. Thus, it creates broken time-reversal symmetry and should translate into magnetic signatures in electrical transport. To confirm this, the magnetoresistance (MR) $\Delta\rho/\rho_{H=0}$ of bilayers was studied using standard Hall bar samples with in-plane magnetic fields. Figure 3(a) shows such a measurement for a Bi$_2$Se$_3$/EuS (1 nm EuS) sample, where an unusual feature consisting of sharp v-shaped dips in the resistance can be seen at 1 K, and duplicated in several other samples. These dips are hysteretic, that is, they appear once for a given direction of the field sweep. The temperature dependence of the magnitude of the MR dip is shown in Fig. 3(b), decreasing as temperature increases. Also plotted here is the field value where the dip occurs, $H_{\text{min}}$, which shows a similar decrease with increasing temperature. The values of $H_{\text{min}}$ are consistent with the $H_C$ values, namely, $H_{\text{min}}$ approaches $H_C \sim 18$ Oe at 4.8 K. These observations point to the ferromagnetic origin of the effect. While the Curie temperature $T_C$ of the bilayer sample is large (~20 K), the hysteretic MR is only visible below around 4 K. Furthermore, the temperature dependence suggests that the hysteretic MR does not arise from charges trapped in EuS, since their conductance contribution would be activated at elevated temperatures, and thus would instead show increasing MR for increasing temperature.

The origin of this hysteretic MR appears to be unconventional, as the resistance always goes through a minimum at
This minimum coincides with the zero net magnetization of the ferromagnetic system where random magnetic domains develop. These random domains are expected to have an isotropic arrangement, consistent with the observed isotropic in-plane MR shown in Fig. 3(a), which is dramatically different from the anisotropic magnetoresistance commonly seen in ferromagnetic materials [32–34]. Moreover, the enhancement of the conductance of Bi2Se3 coinciding with the domain structures at $H_C$ is seen in all Bi2Se3/EuS samples. By applying a perpendicular magnetic field, Fig. 3(c) demonstrates that the saturation moment $M_{PS}$ is even larger compared to $M_{LS}$ in Fig. 2(a). Furthermore, $M_p$ shows a steeper rise with an increasing field in the Bi2Se3/EuS (3 nm) sample compared to the 1 nm EuS grown on Si(111) [Fig. 3(c) inset], even though thicker EuS thin films favor in-plane anisotropy [Fig. 3(c)]. This proves that the perpendicular anisotropy is preferred for EuS films grown on Bi2Se3, which is attributed to the strong spin-orbit coupling of Bi2Se3 [35,36], as well as likely related to the large anisotropy of the $g$ factor for the interface electrons seen in bulk Bi2Se3 [37], and which may result in a canting of the magnetic moment right at the Bi2Se3/EuS interface [Fig. 3(d)]. At $H_C$, domain walls can form in the interface magnetic layer by the formation of randomly oriented magnetic domains [Fig. 3(d)]. The topological surface states at the domain wall would have low mass. The chiral conduction modes are predicted to propagate along the domain wall similar to the quantum Hall edge channels [1,2]. This could enhance the overall conduction in the sample compared to the condition with no domain walls, leading to the resistance dips shown in Fig. 3(a). A similar effect is seen in impurity-doped Bi2Te3 by tuning the Fermi level across its surface Dirac point [13]. However, in the present work this unique property of ferromagnetic TI in heterostructured thin film bilayers is observed even without the electrostatic gating, which could be advantageous for applications. As a result of the induced canted magnetization at the interface, the hysteretic $MR(T)$ could differ from the $M(T)$ of the overall EuS film. Both ferromagnetism of EuS and the coupling between EuS and Bi2Se3 have to be strong to signify this effect. On the other hand, a smaller $T_C$ of the induced interfacial ferromagnetic layer than that of an EuS film can be expected due to possible quantum fluctuations [38], and weakening of the canted interfacial spins, coupled to adjacent in-plane parallel spins, while an increasing temperature may explain the lower onset temperature for the hysteretic MR. Further control of interface quality can be expected to result in higher remnant perpendicular magnetization.

Hall effect data of the control sample (with perpendicular magnetic fields up to 4 T) showed linear magnetic field dependence [Fig. 4(a) inset], which does not change significantly with temperature. For bilayer samples [Figs. 4(a) and 4(b)], the behavior is clearly different, with features exhibiting their ferromagnetic nature. A further consequence of the ferromagnetic conducting interface is the appearance of the anomalous Hall effect (AHE) [39].
not show this sharp rise below $\sim 15$ K in the nonlinear Hall signal. The existence of the anomalous Hall effect further confirms the induced ferromagnetic order in Bi$_2$Se$_3$. Finally, the dominance of the ordinary Hall voltage over the much smaller AHE voltage might be due to the parallel bulk conducting channel of the 20 nm Bi$_2$Se$_3$ that shorts the AHE signal [13]. By reducing the bulk carrier density one could expect a well-defined AHE, as well as a larger hysteretic MR in TI/FI heterostructures.

In summary, Bi$_2$Se$_3$/EuS heterostructures exhibit proximity-induced interfacial magnetization. This effect originates from a uniform exchange field over the TI surface, without structurally disturbing the TI. This local symmetry breaking technique not only enables the creation of cleaner ferromagnetic TI systems with larger surface exchange gaps, superior to the approach with magnetic impurity doping [41] but also allows a greater freedom in nanopatterning lateral TI heterostructures, where designated regions with broken time-reversal symmetry can be created. Similar heterostructures have the potential of developing a variety of technologically advanced devices based on the predicted novel electrical excitations in TI. For example, devices holding zero-field quantum Hall edge channels could be fabricated using TI films sandwiched by FI, as well as systems holding Majorana bound states through the patterning of FI on superconducting TI surfaces.

The authors acknowledge the valuable discussion and assistance of P. A. Lee, L. Fu, J. Shi, S.-Q. Shen, G.-X. Miao, and H.-Z. Lu. We would like to thank the MIT MRSEC for support through the MRSEC Program of the NSF under Grant No. DMR-0819762. Part of this work was carried out at the CMSE shared experimental facilities. P. W. and J. S. M. thank the NSF for support from the NSF under Grant No. DMR-0819762. Part of this work was carried out at the CMSE shared experimental facilities. P. W. and J. S. M. thank the NSF for support from the NSF under Grant No. DMR-0819762. Part of this work was carried out at the CMSE shared experimental facilities. P. W. and J. S. M. thank the NSF for support from N00014-09-1-0177 and N00014-13-1-0301. B. A. A. and D. H. thank the NSF for support from DMR Grant No. 0907007.

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